

Complementary Silicon Plastic Power Transistors

TIP41G, TIP41AG, TIP41BG, TIP41CG (NPN), TIP42G, TIP42AG, TIP42BG, TIP42CG (PNP)

Designed for use in general purpose amplifier and switching applications.

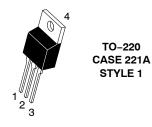
Features

- Epoxy Meets UL 94 V-0 @ 0.125 in
- These Devices are Pb-Free and are RoHS Compliant*

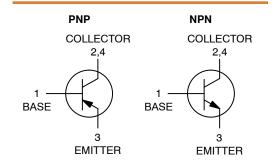
MAXIMUM RATINGS

Symbol	Rating	Value	Unit	
V _{CEO}	Collector-Emitter Voltage TIP41G, TIP42G TIP41AG, TIP42AG TIP41BG, TIP42BG TIP41CG, TIP42CG	40 60 80 100	Vdc	
V _{CB}	Collector-Base Voltage TIP41G, TIP42G TIP41AG, TIP42AG TIP41BG, TIP42BG TIP41CG, TIP42CG	40 60 80 100	Vdc	
V _{EB}	Emitter-Base Voltage	5.0	Vdc	
I _C	Collector Current - Continuous	6.0	Adc	
I _{CM}	Collector Current - Peak	10	Adc	
I _B	Base Current	2.0	Adc	
P _D	Total Power Dissipation @ T _C = 25°C Derate above 25°C	65 0.52	W W/°C	
P _D	Total Power Dissipation @ T _A = 25°C Derate above 25°C	2.0 0.016	W W/°C	
Е	Unclamped Inductive Load Energy (Note 1)	62.5	mJ	
T _J , T _{stg}	Operating and Storage Junction, Temperature Range	-65 to +150	°C	
HBM	ESD - Human Body Model	3B	V	
MM	ESD - Machine Model	С	V	

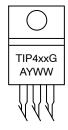
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



6 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 40-60-80-100 VOLTS, 65 WATTS



MARKING DIAGRAM



TIP4xx = Device Code xx = 1, 1A, 1B, 1C 2, 2A, 2B, 2C A = Assembly Location Y = Year

Y = Year WW = Work Week G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 6.

^{1.} I_C = 2.5 A, L = 20 mH, P.R.F. = 10 Hz, V_{CC} = 10 V, R_{BE} = 100 Ω .

^{*}For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, <u>SOLDERRM/D</u>.

THERMAL CHARACTERISTICS

Symbol	Characteristic	Max	Unit
$R_{ heta JC}$	Thermal Resistance, Junction-to-Case	1.67	°C/W
$R_{ heta JA}$	Thermal Resistance, Junction-to-Ambient	57	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Min	Characteristic	Symbol	Max	Unit
FF CHARA	CTERISTICS			
40 60 80 100	Collector-Emitter Sustaining Voltage (Note 2) (I _C = 30 mAdc, I _B = 0) TIP41G, TIP42G TIP41AG, TIP42AG TIP41BG, TIP42BG TIP41CG, TIP42CG	V _{CEO(sus)}	- - - -	Vdc
-	Collector Cutoff Current $(V_{CE}=30\ Vdc,\ I_B=0)$ TIP41G, TIP41AG, TIP42G, TIP42AG $(V_{CE}=60\ Vdc,\ I_B=0)$ TIP41BG, TIP41CG, TIP42BG, TIP42CG	I _{CEO}	0.7 0.7	mAdc
- - -	Collector Cutoff Current $ (V_{CE} = 40 \text{ Vdc}, V_{EB} = 0) $ $ \text{TIP41G}, \text{TIP42G} $ $ (V_{CE} = 60 \text{ Vdc}, V_{EB} = 0) $ $ \text{TIP41AG}, \text{TIP42AG} $ $ (V_{CE} = 80 \text{ Vdc}, V_{EB} = 0) $ $ \text{TIP41BG}, \text{TIP42BG} $ $ (V_{CE} = 100 \text{ Vdc}, V_{EB} = 0) $ $ \text{TIP41CG}, \text{TIP42CG} $	I _{CES}	400 400 400 400	μAdc
-	Emitter Cutoff Current (V _{BE} = 5.0 Vdc, I _C = 0)	I _{EBO}	1.0	mAdc
N CHARAC	CTERISTICS (Note 2)			
30 15	DC Current Gain ($I_C = 0.3$ Adc, $V_{CE} = 4.0$ Vdc) ($I_C = 3.0$ Adc, $V_{CE} = 4.0$ Vdc)	h _{FE}	- 75	-
-	Collector-Emitter Saturation Voltage (I _C = 6.0 Adc, I _B = 600 mAdc)	V _{CE(sat)}	1.5	Vdc
	Base–Emitter On Voltage (I _C = 6.0 Adc, V _{CE} = 4.0 Vdc)	V _{BE(on)}	2.0	Vdc
YNAMIC C	HARACTERISTICS			
3.0	Current-Gain – Bandwidth Product (I _C = 500 mAdc, V _{CE} = 10 Vdc, f _{test} = 1.0 MHz)	f _T	-	MHz
20	Small-Signal Current Gain (I _C = 0.5 Adc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{fe}	-	-

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

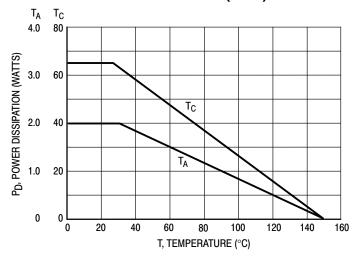
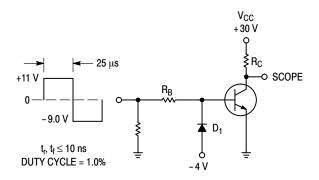


Figure 1. Power Derating



 ${\rm R}_{\rm B}$ and ${\rm R}_{\rm C}$ varied to obtain desired current levels

D $_1$ MUST BE FAST RECOVERY TYPE, e.g.: 1N5825 USED ABOVE I $_B\approx 100$ mA MSD6100 USED BELOW I $_B\approx 100$ mA

Figure 2. Switching Time Test Circuit

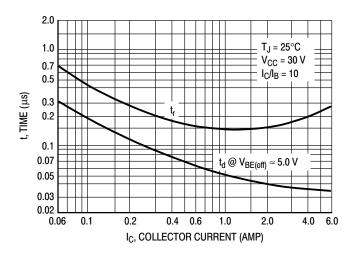


Figure 3. Turn-On Time

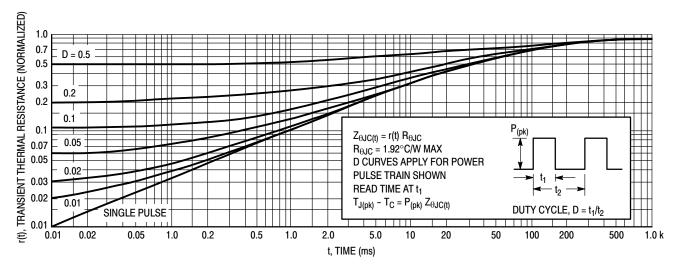


Figure 4. Thermal Response

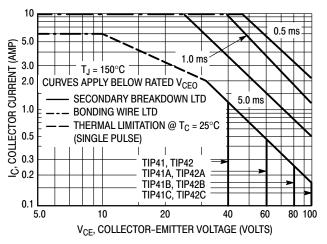
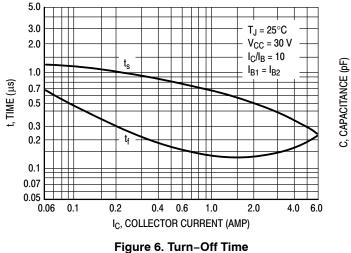


Figure 5. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.



300 200 200 T_J = 25°C T_J = 25°C T_J = 25°C C_{ib}

C_{ob}

30
0.5 1.0 2.0 3.0 5.0 10 20 30 50

V_B, REVERSE VOLTAGE (VOLTS)

Figure 7. Capacitance

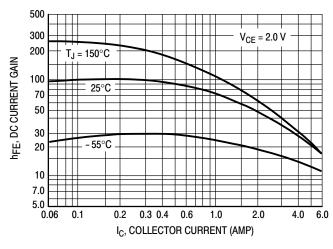


Figure 8. DC Current Gain

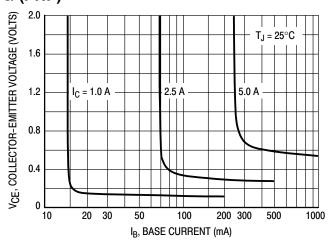


Figure 9. Collector Saturation Region

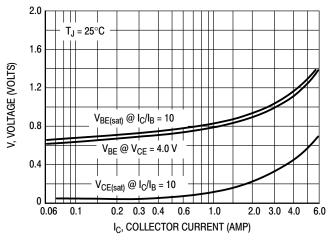


Figure 10. "On" Voltages

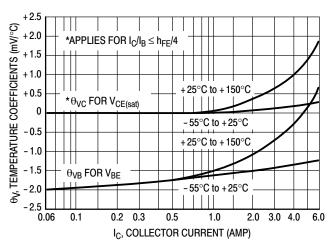


Figure 11. Temperature Coefficients

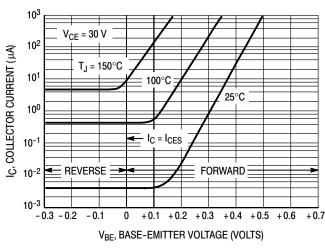


Figure 12. Collector Cut-Off Region

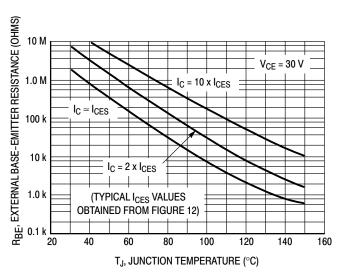


Figure 13. Effects of Base-Emitter Resistance

ORDERING INFORMATION

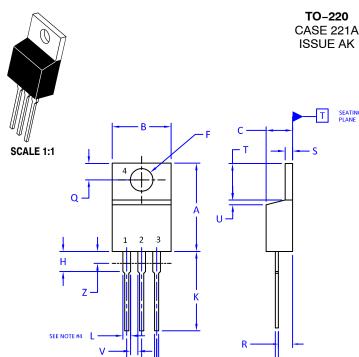
Device	Package	Shipping
TIP41BG	TO-220 (Pb-Free)	50 Units / Rail
TIP41CG	TO-220 (Pb-Free)	50 Units / Rail
TIP42AG	TO-220 (Pb-Free)	50 Units / Rail
TIP42CG	TO-220 (Pb-Free)	50 Units / Rail

DISCONTINUED (Note 3)

TIP41G	TO-220 (Pb-Free)	50 Units / Rail
TIP41AG	TO-220 (Pb-Free)	50 Units / Rail
TIP42G	TO-220 (Pb-Free)	50 Units / Rail
TIP42BG	TO-220 (Pb-Free)	50 Units / Rail

^{3.} **DISCONTINUED:** These devices are not recommended for new design. Please contact your **onsemi** representative for information. The most current information on these devices may be available on www.onsemi.com.





CASE 221A

DATE 13 JAN 2022

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: INCHES
- 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

4. MAX WIDTH FOR F102 DEVICE = 1.35MM

	INCHES		MILLIMETERS	
DIM	MIN.	MAX.	MIN.	MAX.
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
К	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

STYLE 1: PIN 1. 2. 3. 4.	BASE COLLECTOR EMITTER COLLECTOR	STYLE 2: PIN 1. 2. 3. 4.		STYLE 3: PIN 1. 2. 3. 4.	CATHODE ANODE GATE ANODE	STYLE 4: PIN 1. 2. 3. 4.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE MAIN TERMINAL 2
STYLE 5: PIN 1. 2. 3. 4.	GATE DRAIN SOURCE DRAIN	STYLE 6: PIN 1. 2. 3. 4.	ANODE CATHODE ANODE CATHODE	STYLE 7: PIN 1. 2. 3. 4.	ANODE	2. 3.	CATHODE ANODE EXTERNAL TRIP/DELAY ANODE
STYLE 9: PIN 1. 2. 3. 4.	GATE COLLECTOR EMITTER COLLECTOR	STYLE 10: PIN 1. 2. 3. 4.	GATE	STYLE 11: PIN 1. 2. 3. 4.		STYLE 12 PIN 1. 2. 3. 4.	MAIN TERMINAL 1 MAIN TERMINAL 2

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